

**DAP202U** SWITCHING DIODE

**FEATURES:**

Power dissipation

 P<sub>D</sub>: 200 mW (T<sub>amb</sub>=25°C)

Collector current

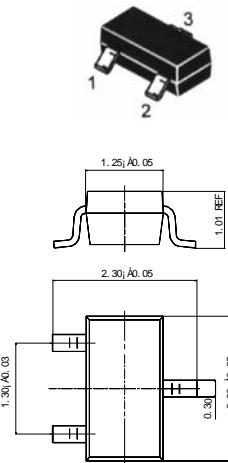
 I<sub>F</sub>: 100 mA

Collector-base voltage

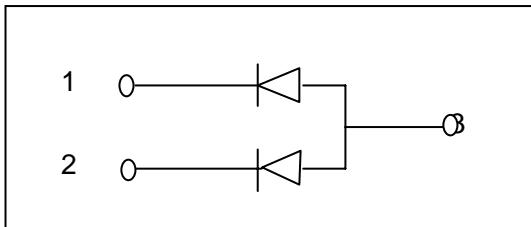
 V<sub>R</sub>: 80 V

Operating and storage junction temperature range

 T<sub>J</sub>, T<sub>stg</sub>: -55°C to +150°C

**SOT-323**


Unit mm

**CIRCUIT:**

**MARKING:** P

**ELECTRICAL CHARACTERISTICS (T<sub>amb</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	V <sub>(BR)</sub>	I <sub>R</sub> = 100µA	80		V
Reverse voltage leakage current	I <sub>R</sub>	V <sub>R</sub> =70V		0.1	µA
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =100mA		1.2	V
Diode capacitance	C <sub>D</sub>	V <sub>R</sub> =6V, f=1MHz		3.5	pF
Reverse recovery time	t <sub>rr</sub>	V <sub>R</sub> =6V, I <sub>F</sub> =5mA		4	ns